

2SA1327

SILICON PNP EPITAXIAL TYPE (PCT PROCESS)

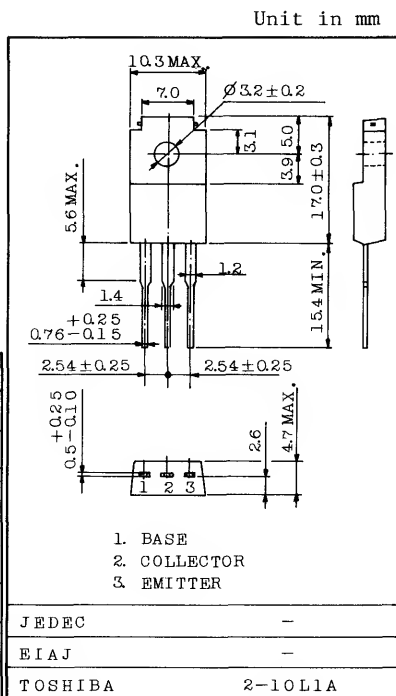
STROBO FLASH APPLICATIONS.
AUDIO POWER AMPLIFIER APPLICATIONS.

FEATURES:

- . MIN. h_{FE} of 70 at -2V, -8A
- . -10A Rated Collector Current
- . MAX. $V_{CE(sat)}$ of -0.5V at -8A I_C
- . 20W at 25°C Case Temperature

MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		V_{CB0}	-50	V
Collector-Emitter Voltage		V_{CE0}	-20	V
Emitter-Base Voltage		V_{EB0}	-8	V
Collector Current	DC	I_C	-10	A
	Pulse	I_{CP}	-20	A
Base Current		I_B	-2	A
Collector Power Dissipation	Ta=25°C	P_C	2.0	W
	Tc=25°C		20	W
Junction Temperature		T_j	150	°C
Storage Temperature Range		T_{stg}	-55 ~ 150	°C



Weight : 2.1g

ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CB0}	$V_{CB}=-50V, I_E=0$	-	-	-1.0	μA
Emitter Cut-off Current	I_{EB0}	$V_{EB}=-8V, I_C=0$	-	-	-1.0	μA
Collector-Emitter Brakdown Voltage	V_{CE0}	$I_C=-10mA, I_B=0$	-20	-	-	V
DC Current Gain	$h_{FE(1)}$ (Note)	$V_{CE}=-2V, I_C=-1A$	100	-	320	
	$h_{FE(2)}$	$V_{CE}=-2V, I_C=-8A$	70	140	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-8A, I_B=-0.4A$	-	-0.3	-0.5	V
Base-Emitter Voltage	V_{BE}	$V_{CE}=-2V, I_C=-8A$	-	-0.95	-0.5	V
Transition Frequency	f_T	$V_{CE}=-2V, I_C=-1A$	-	45	-	MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=-10V, I_E=0, f=1MHz$	-	400	-	pF

Note : $h_{FE(1)}$ Classification 0 : 100 ~ 200, Y : 160 ~ 320

